WEST Search History

DATE: Sunday, November 10, 2002

Set Name Query side by side		Hit Count	Set Name result set
DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=ADJ			
L10	(ALE or ALD or (atomic layer near2 (deposit\$3 or epitax\$5))) and (cold wall)	38	L10
L9	(ALE or ALD or (atomic layer near2 (deposit\$3 or epitax\$5))) and (hot wall)	29	L9
DB=USPT; PLUR=YES; OP=ADJ			
L8	4570328.pn.	1	L8
DB=JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=ADJ			
L7	(\$3CVD or (vapor deposit\$3) or ALE or ALD or (atomic layer near2 (deposit\$3 or epitax\$5))) and ((chamber or reactor or wall or vessell or vessel) near4 (temperature) near4 (higher or hotter) near4 (substrate or wafer or sample or pedestal or support or chuck or susceptor))	8	L7
$DB=USPT,PGPB;\ PLUR=YES;\ OP=ADJ$			
L6	(\$3CVD or (vapor deposit\$3) or ALE or ALD or (atomic layer near2 (deposit\$3 or epitax\$5))) and ((chamber or reactor or wall or vessell or vessel) near4 (temperature) near4 (higher or hotter) near4 (substrate or wafer or sample or pedestal or support or chuck or susceptor))	104	L6
L5	(\$3CVD or (vapor deposit\$3) or ALE or ALD or (atomic layer near2 (deposit\$3 or epitax\$5))) and ((chamber or reactor or wall or vessell or vessel) near8 (temperature) near8 (higher or lower or hotter or colder or different) near8 (substrate or wafer or sample or pedestal or support or chuck or susceptor)) and ((control\$5 or regulat\$5) near4 temperature near4 (chamber or reactor or wall or vessell) and ((control\$5 or regulat\$5) near4 temperature near4 (substrate or wafer or sample or pedestal or support or chuck or susceptor))	112	L5
$DB=JPAB,EPAB,DWPI,TDBD;\ PLUR=YES;\ OP=ADJ$			
L4	(\$3CVD or (vapor deposit\$3) or ALE or ALD or (atomic layer near2 (deposit\$3 or epitax\$5))) and ((chamber or reactor or wall or vessell or vessel) near8 (temperature) near8 (higher or lower or hotter or colder or different) near8 (substrate or wafer or sample or pedestal or support or chuck or susceptor))	61	L4
$DB=USPT,PGPB;\ PLUR=YES;\ OP=ADJ$			
L3	L2 and (\$3CVD or (vapor deposit\$3) or ALE or ALD or (atomic layer near2 (deposit\$3 or epitax\$5))) and ((chamber or reactor or wall or vessell or vessel) near8 (temperature) near8 (higher or lower or hotter or colder or different) near8 (substrate or wafer or sample or pedestal or support or chuck or susceptor)) ((427/248.1).icls. or (427/255.23).icls. or (427/255.28).icls. or	170	L3

L2 (427/255.7).icls. or (427/587).icls. or (118/715).icls. or (118/719).icls. or (118/724).icls. or (118/725).icls. or (118/728).icls. or (117/88).icls. or ((117/105)!.ICLS.))

5862 L2

L1 a

6765631

L1

END OF SEARCH HISTORY